

# RT3T77M

Composite Transistor With Resistor  
For Switching Application  
Silicon Epitaxial Type

## DESCRIPTION

RT3T77M is composite transistor built with RT1N140 chip and RT1P140 chip in SC-88 package.

## FEATURE

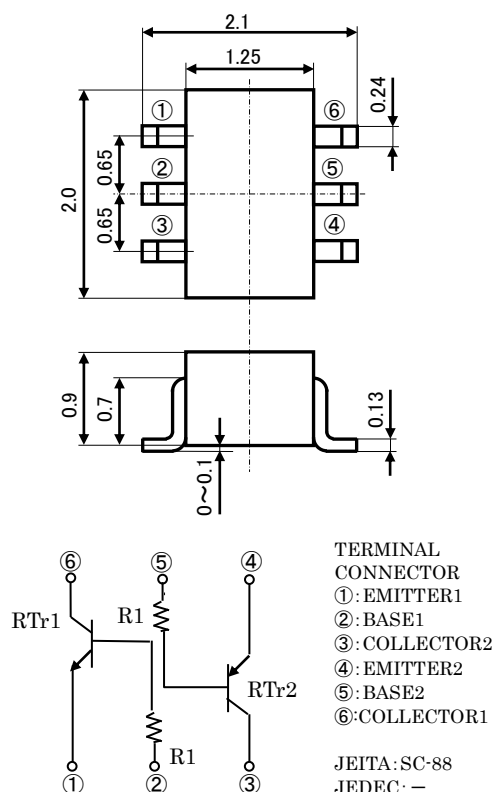
Built-in bias resistor (R1=10k $\Omega$ )  
Mini package for easy mounting

## APPLICATION

Inverted circuit, Switching circuit,  
Interface circuit, Driver circuit

## OUTLINE DRAWING

Unit:mm

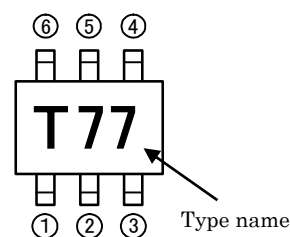


## MAXIMUM RATING (Ta=25°C) (RTr1\_NPN, RTr2\_PNP)

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CB0</sub>	Collector to Base voltage	50	V
V <sub>EB0</sub>	Emitter to Base voltage	6	V
V <sub>CEO</sub>	Collector to Emitter voltage	50	V
I <sub>C</sub>	Collector current	100	mA
I <sub>CM</sub>	Peak Collector current	200	mA
P <sub>T</sub>	Total dissipation	200	mW
T <sub>j</sub>	Junction temperature	+150	°C
T <sub>stg</sub>	Storage temperature	-55~+150	°C

※PNP built in transistor of "—" sign is abbreviation.

## MARKING



## ELECTRICAL CHARACTERISTICS (Ta=25°C) (RTr1\_NPN, RTr2\_PNP)

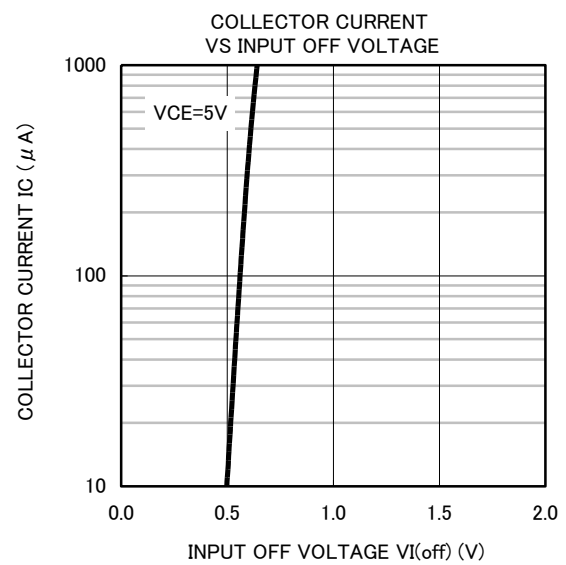
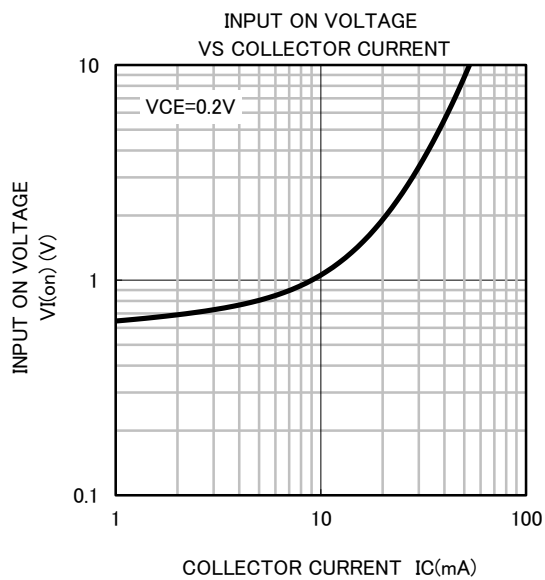
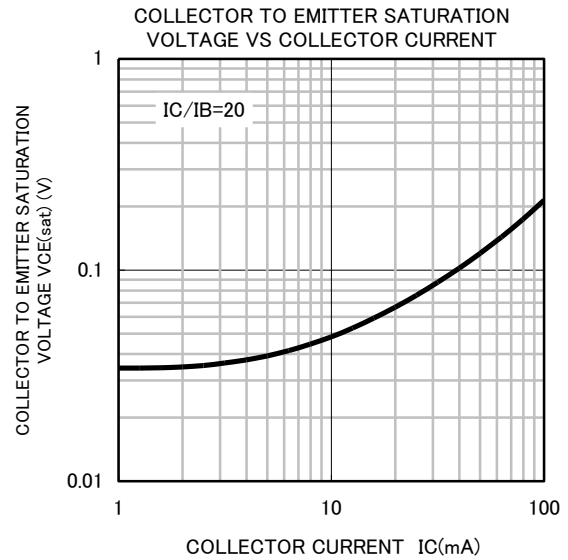
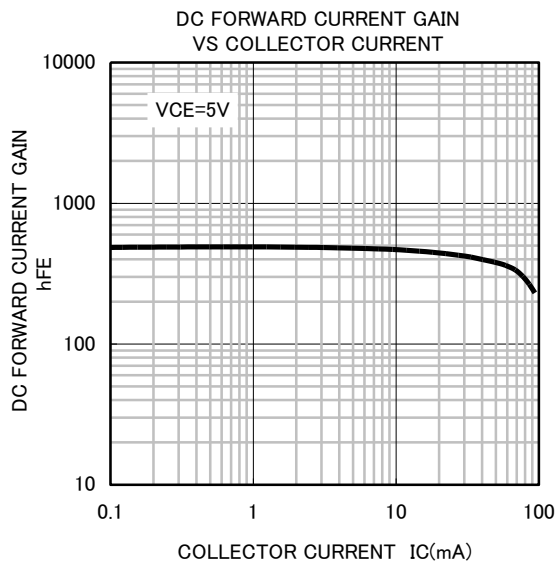
Symbol	Parameter	Test conditions	Limits			Unit	
			Min	Typ	Max		
V <sub>(BR)CEO</sub>	Collector to Emitter breakdown voltage	I <sub>C</sub> =100 $\mu$ A, R <sub>BE</sub> = $\infty$	50	—	—	V	
I <sub>CB0</sub>	Collector cut off current	V <sub>CB</sub> =50V, I <sub>E</sub> =0	—	—	0.1	$\mu$ A	
I <sub>EB0</sub>	Emitter cut off current	V <sub>EB</sub> =5V, I <sub>C</sub> =0	—	—	0.1	$\mu$ A	
h <sub>FE</sub>	DC forward current gain	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	100	—	—	—	
V <sub>CE(sat)</sub>	Collector to Emitter saturation voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA	—	0.1	0.3	V	
R <sub>1</sub>	Input resistor	—	7	10	13	k $\Omega$	
f <sub>T</sub>	Gain band width product	V <sub>CE</sub> =6V, I <sub>E</sub> =10mA	RTr1	—	200	—	MHz
			RTr2	—	150	—	

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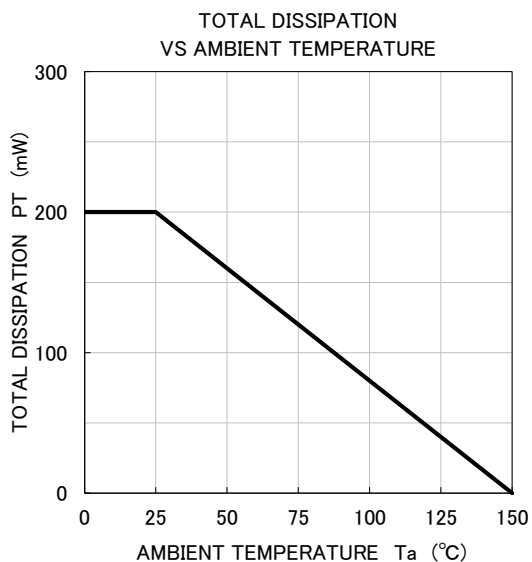
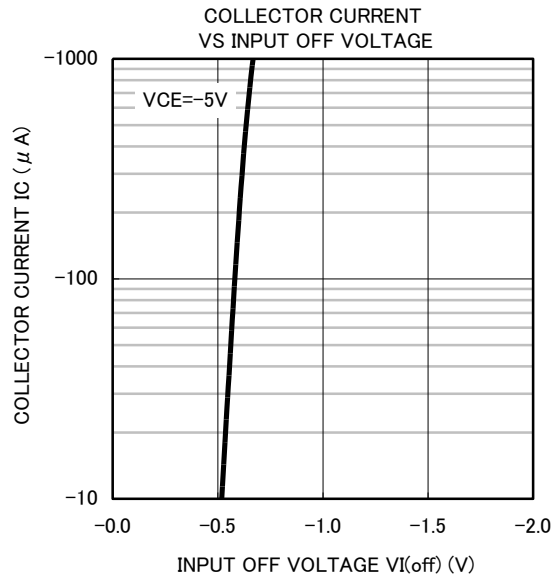
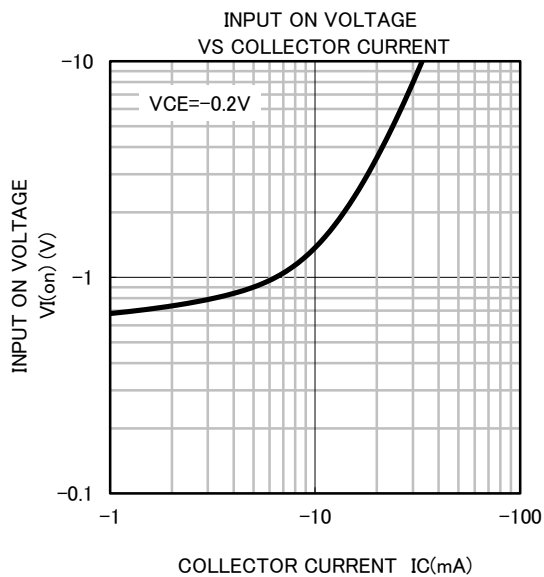
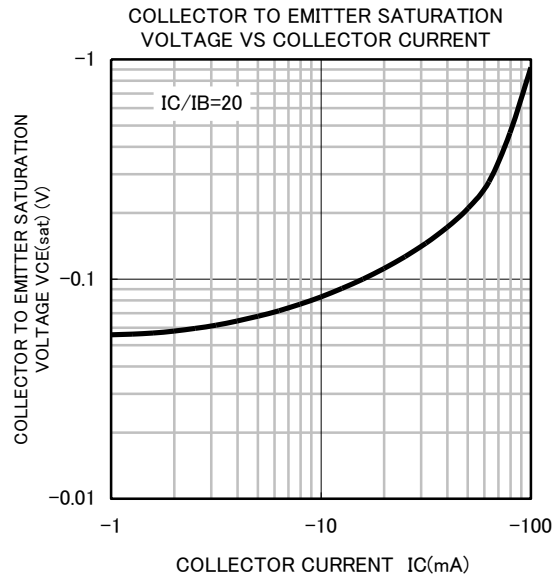
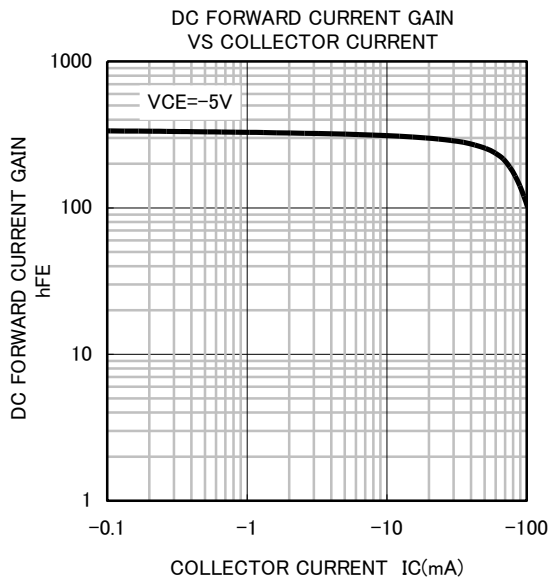
## TYPICAL CHARACTERISTICS(Ta=25°C)(RTr1\_NPN)



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## TYPICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ ) (RTr 2\_PNP)



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